GJSBL630CT~660CT

SCHOTTKY BARRIER RECTIFIERS

REVERSE VOLTAGE 30V TO 60V, CURRENT 6A

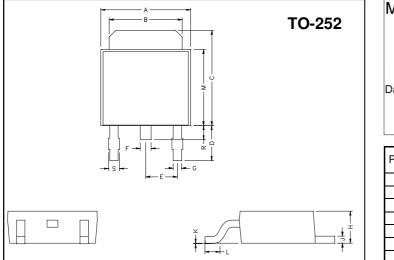
Description

The GJSBL630CT~660CT are designed for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

Features

- Guard ring for transient protection
- Low power loss, high efficiency
- High current capability, low VF
- High surge capacity

Package Dimensions



Marking :	Circuit : BASE O COMMON 2 CATHODE
35V.35 40V.40 45V.45 50V.50 60V.60 ← 6□□CT	
	ANODE COMMON ANODE

	Millim	otor	1	Millimator		
REF.	Millimeter		REF.	Millimeter		
	Min.	Max.		Min.	Max.	
Α	6.40	6.80	G	0.50	0.70	
В	5.20	5.50	Н	2.20	2.40	
С	6.80	7.20	J	0.45	0.55	
D	2.40	3.00	K	0	0.15	
ш	2.30 REF.		L	0.90	1.50	
F	0.70	0.90	М	5.40	5.80	
S	0.60	0.90	R	0.80	1.20	

Maximum Ratings and Electrical Characteristics at Ta=25°C unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%

	Symbol	Ratings					Unit	
Parameters		GJSBL 630CT	GJSBL 635CT	GJSBL 640CT	GJSBL 645CT	GJSBL 650CT	GJSBL 660CT	V
Max. Recurrent Peak Reverse Voltage	V _{RRM}	30	35	40	45	50	60	V
Max. RMS Voltage	V _{RMS}	21	24.5	28	31.5	35	42	V
Max. DC Blocking Voltage	V _{DC}	30	35	40	45	50	60	V
Max. Average Forward @T _c =95°C Rectified Current (See Fig.1)	I _(AV)	6				А		
Peak Surge Forward Current 8.3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I _{FSM}	75				A		
Max. Forward Voltage @ 3A (Note 1)	V _F	0.55 0.7				V		
Max. DC Reverse Current @Tj=25°C At Rated DC Blocking Voltage @Tj=100°C	I _R	0.5 50				mA		
Typical Thermal Resistance @Tc=25°C (Note2)	R _{eJC}	20				°C/W		
Operating Temperature Range	Tj	-55 ~ +125				°C		
Storage Temperature Range	Tstg	-55 ~ +150				°C		

Notes: 1. 300us Pulse Width, 2% Duty Cycle.

2. Thermal Resistance Junction to Case.

ISSUED DATE :2006/05/11 REVISED DATE :

Characteristics Curve

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1.0

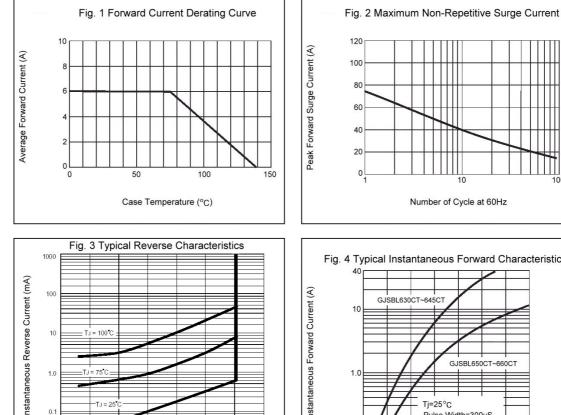
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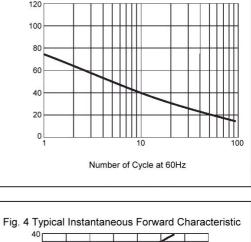
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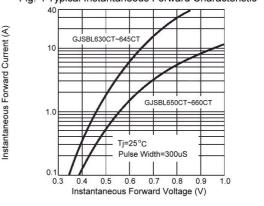
TJ = 100°C

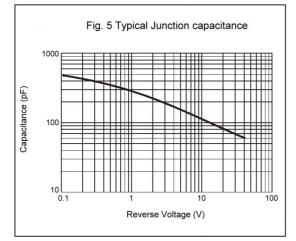
-TJ = 75°

TJ = 2









Percent of Rated Peak Reverse Voltage (%)

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